

KSC2786

TV PIF Amplifier, FM Tuner RF Amplifier, Mixer, Oscillator

High Current Gain Bandwidth Product : f_T=600MHz (TYP.)
 High Power Gain : G_{PE}=22dB at f=100MHz



1.Emitter 2. Collector 3. Base

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	20	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current	20	mA
P _C	Collector Power Dissipation	250	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =10μA, I _E =0	30			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =5mA, I _B =0 20				V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =10μA, I _C =0	4			V
I _{CBO}	Collector Cut-off Current	V_{CB} =30V, I_{E} =0			0.1	μΑ
I _{EBO}	Emitter Cut-off Current	V_{EB} =4V, I_{C} =0			0.1	μΑ
h _{FE}	DC Current Gain	V _{CE} =6V, I _C =1mA	40		240	
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =6V, I _C =1mA		0.72		V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =1mA		0.1	0.3	V
f _T	Current Gain Bandwidth Product	V _{CE} =6V, I _C =1mA	400	600		MHz
C _{ob}	Output Capacitance	V _{CB} =6V, I _E =0, f=1MHz		1.2		pF
C _{c·rbb} ,	Collector-Base Time Constant	V _{CE} =6V, I _C =1mA f=31.9MHz		12	15	ps
NF	Noise Figure	V_{CE} =6V, I_{C} =1mA R_{S} =50 Ω , f=100MHz		3.0	5.0	dB
G _{PE}	Power Gain	V _{CE} =6V, I _C =1mA f=100MHz	18	22		dB

h_{FE} Classification

Classification	R	0	Y
h _{FE}	40 ~ 80	70 ~ 140	120 ~ 240

Typical Characteristics

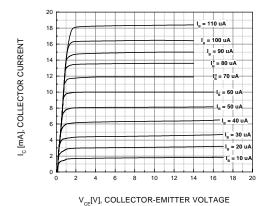


Figure 1. Static Characteristics

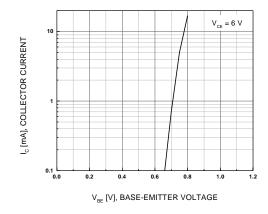


Figure 2. Base-Emitter On Voltage

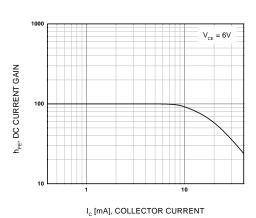


Figure 3. DC Current Gain

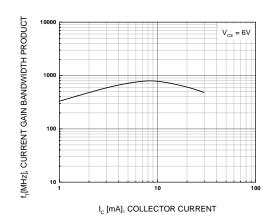


Figure 4. f_T - I_C

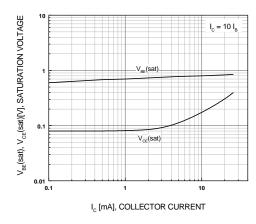


Figure 5. Saturation Voltage

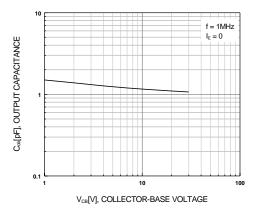
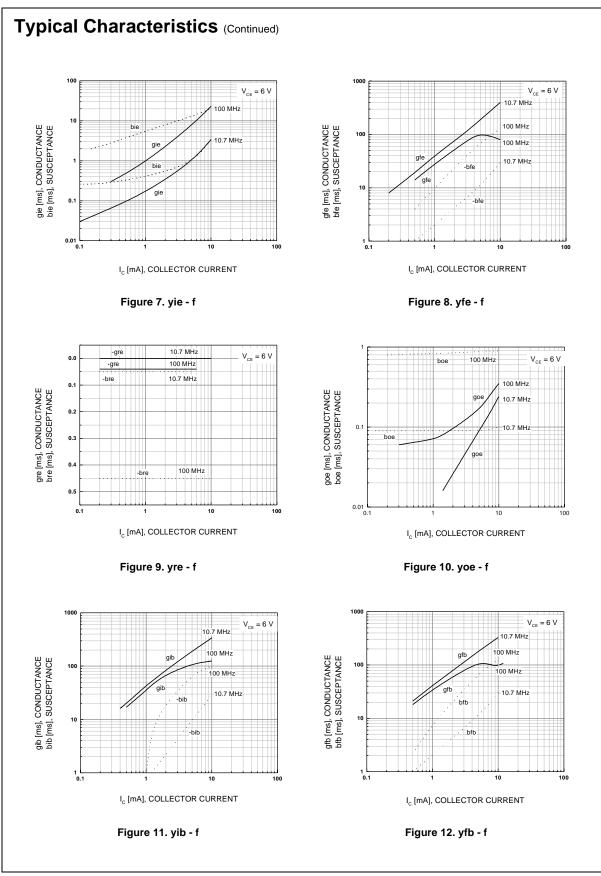
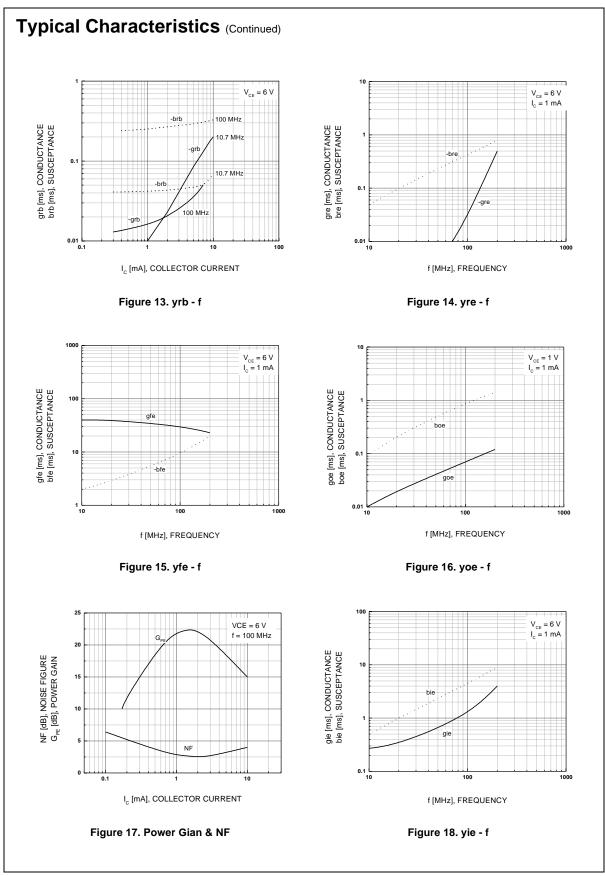


Figure 6. Output Capacitance

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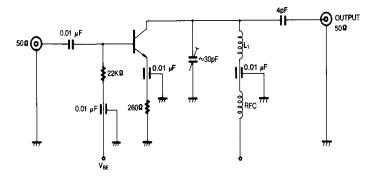
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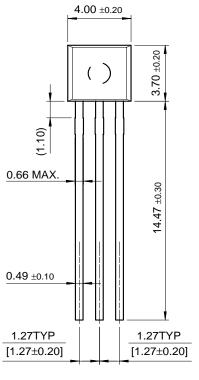
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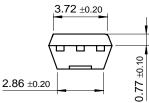
Typical Characteristics (Continued)

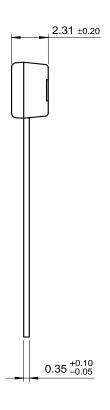
100MHz Gpe, NF TEST CIRCUIT



TO-92S







Dimensions in Millimeters

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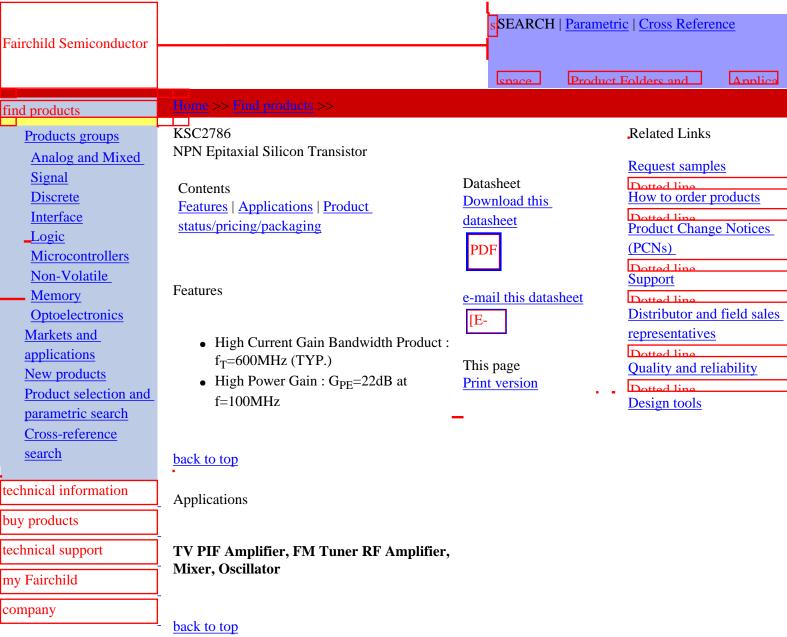
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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSC2786OBU	Full Production	\$0.053	<u>TO-92S</u>	3	BULK
KSC2786RTA	Full Production	\$0.053	<u>TO-92S</u>	3	TAPE REEL
KSC2786OTA	Full Production	\$0.053	<u>TO-92S</u>	3	TAPE REEL
KSC2786RBU	Full Production	\$0.053	<u>TO-92S</u>	3	BULK
KSC2786YTA	Full Production	\$0.053	<u>TO-92S</u>	3	TAPE REEL
KSC2786YBU	Full Production	\$0.053	<u>TO-92S</u>	3	BULK

^{* 1,000} piece Budgetary Pricing

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